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ABSTRACT:

PURPOSE: To make a length of a fuse long by making use of a difference in level, to reduce a required area and to make a chip size small by a method wherein an uneven part is formed on the surface of an oxide film with which the surface of a silicon substrate is covered.

CONSTITUTION: An oxide film 15 having a part whose thickness differs sharply is formed on the surface of a silicon substrate 3. Polycrystalline silicon 4 and another oxide film 15' are grown on the surface of the film 15 to form electrodes 1, 2' the oxide film 15' between them is etched

and removed. A  
length of a fuse formed by the polycrystalline silicon 4  
becomes long by a  
difference in level, and a required area can be made small.

Consequently, a  
chip size of an integrated circuit provided with the fuse  
can be reduced.

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## PATENT ABSTRACTS OF JAPAN

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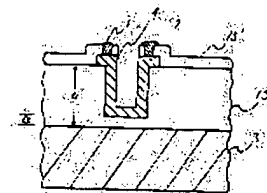
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### (54) INTEGRATED CIRCUIT DEVICE

#### (57)Abstract:

PURPOSE: To make a length of a fuse long by making use of a difference in level, to reduce a required area and to make a chip size small by a method wherein an uneven part is formed on the surface of an oxide film with which the surface of a silicon substrate is covered.

CONSTITUTION: An oxide film 15 having a part whose thickness differs sharply is formed on the surface of a silicon substrate 3. Polycrystalline silicon 4 and another oxide film 15' are grown on the surface of the film 15 to form electrodes 1, 2' the oxide film 15' between them is etched and removed. A length of a fuse formed by the polycrystalline silicon 4 becomes long by a difference in level, and a required area can be made small. Consequently, a chip size of an integrated circuit provided with the fuse can be reduced.



### LEGAL STATUS

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